Electronic Supplementary Material (ESI) for Faraday Discussions. This journal is © The Royal Society of Chemistry 2016

## Supporting Information.

## Stable hybrid organic/inorganic photocathodes for hydrogen evolution with amorphous WO<sub>3</sub> hole selective contact.

Alessandro Mezzetti, <sup>1,2</sup> Fumagalli Francesco, <sup>1</sup> Antonio Alfano, <sup>1,3</sup> Daniele Iadicicco, <sup>1,4</sup> Maria Rosa Antognazza <sup>1</sup> and Fabio di Fonzo. <sup>1,\*</sup>

To convert from the measured reference electrode potential (versus Ag/AgCl in saturated KCl) to the reversible hydrogen electrode (RHE) potential, the following equation is used:

$$E_{RHE} = E_{Ag/AgCl} + 0.0591 \times pH + E_{Ag/AgCl}^{\phantom{A}0} \quad \left[ E_{Ag/AgCl}^{\phantom{A}0} = + \ 0.1976 \ V \right]$$

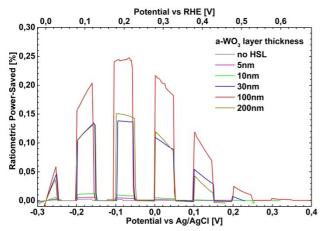


Figure S1. Ratiometric power saved curves as a function of the applied bias for a series of hybrid organic photocathodes with varying thickness of the amorphous WO<sub>3</sub> layer. The peak of the curve is the maximum power point in the corresponding linear sweep voltammetry curve.

The depletion layer with  $x_d$  is calculated with the following equation, derived from Poisson's equations under the full depletion approximation for a metal/semiconductor junction:

$$x_d = \sqrt{\frac{2\varepsilon_s(\varphi_m - \varphi_s)}{qN_d}}$$
 [Eq. S1]

where  $\varepsilon_s$  is the relative dielectric permittivity of the semiconductor,  $\varphi_{m/s}$  is the work function of the metal and of the semiconductor, q is the electron charge and  $N_d$  is the donor density of the semiconductor.

<sup>&</sup>lt;sup>1</sup> Center for Nano Science and Technology@PoliMi, Istituto Italiano di Tecnologia, Via Pascoli 70/3, 20133 Milano, Italy.

<sup>&</sup>lt;sup>2</sup> Politecnico di Milano, Dipartimento di Fisica, P.zza L. da Vinci 32, 20133 Milano, Italy.

<sup>&</sup>lt;sup>3</sup> Politecnico di Milano, Dipartimento di Chimica, Materiali e Ingegneria Chimica "Giulio Natta", Piazza Leonardo da Vinci, 32, 20133 Milano, Italy

<sup>&</sup>lt;sup>4</sup> Politecnico di Milano, Dipartimento di Energia, Via Ponzio 34/3, 20133 Milano, Italy.

<sup>\*</sup> Corresponding author, e-mail: fabio.difonzo@iit.it

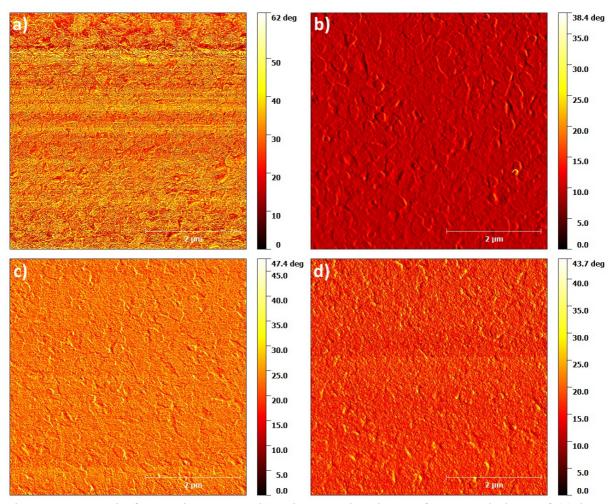


Figure S2. Atomic force microscopy phase images showing surface morphology of (a) bare ITO and (b-d) ITO/WO<sub>3</sub> with different WO<sub>3</sub> HSL thickness (5 nm, 30 nm and 100 nm respectively).

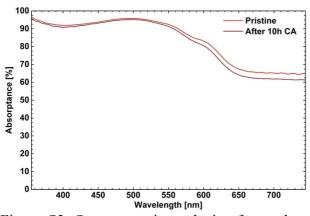


Figure S3. Spectroscopic analysis of complete photocathode architecture showing the UV-Vis-nIR absorptance spectra of a pristine device and of a device that has undergone a 10-hour chronoamperometry.